



PATENT ABSTRACTS OF JAPAN

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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract

PROBLEM TO BE SOLVED: To provide a manufacturing method for a MOSFET which restrains external resistance and thermal resistance.

SOLUTION: A drain electrode pad on a pellet 10 on which a MOSFET circuit is formed is connected to a header 41 by high melting-point solder. A gate electrode pad and a source electrode pad on the pellet 10 are connected to an inner lead 36 and an inner lead 37 by connection parts 25, 28 which are composed of solder bumps of low melting-point solder. The source electrode pad is connected to the source inner lead 37 by a plurality of connection points 26. As a result, when a gate electrode and a source electrode are connected directly to the respective inner leads 36, 37 by the respective connection parts 26, external resistance can be reduced as compared with an electric connection by using a wire. When the source electrode is connected to inner leads 36, 37 by the plurality of connection parts 26, external resistance on can be reduced. Since the header 41 and the inner leads

36, 37 as a group are separate bodies, a best material can be used for the inner leads 36, 37 and the header 41, and the performance of a product can be enhanced.

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